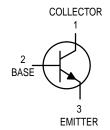
Amplifier Transistors NPN Silicon



MAXIMUM RATINGS

Rating	Symbol	BC 182	BC 183	BC 184	Unit
Collector-Emitter Voltage	VCEO	50	30	30	Vdc
Collector-Base Voltage	VCBO	60	45	45	Vdc
Emitter-Base Voltage	VEBO		6.0		Vdc
Collector Current — Continuous	IC	100		mAdc	
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	350 2.8		mW mW/°C	
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.0 8.0		Watts mW/°C	
Operating and Storage Junction Temperature Range	T _J , T _{Stg}	-5	5 to +1	50	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I _C = 2.0 mA, I _B = 0)	BC182 BC183 BC184	V(BR)CEO	50 30 30	_ _ _	_ _ _	٧
Collector–Base Breakdown Voltage (I _C = 10 μA, I _E = 0)	BC182 BC183 BC184	V(BR)CBO	60 45 45	_ _ _ _	_ _ _	V
Emitter-Base Breakdown Voltage (I _E = 100 μA, I _C = 0)		V(BR)EBO	6.0	_	_	V
Collector Cutoff Current (V _{CB} = 50 V, V _{BE} = 0) (V _{CB} = 30 V, V _{BE} = 0)	BC182 BC183 BC184	ICBO	_ _ _	0.2 0.2 0.2	15 15 15	nA
Emitter–Base Leakage Current (VEB = 4.0 V, IC = 0)		IEBO	_	_	15	nA

BC182,A,B BC183 BC184



BC182,A,B BC183 BC184

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS						
DC Current Gain (I _C = 10 μ A, V _{CE} = 5.0 V)	BC182 BC183 BC184	hFE	40 40 100	_ _ _	_ _ _	_
$(I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC182 BC183 BC184		120 120 250	_ _ _	500 800 800	
$(I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC182 BC183 BC184		80 80 130	_ _ _	_ _ _	
Collector-Emitter On Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA) ⁽¹⁾		VCE(sat)	_ _ _	0.07 0.2	0.25 0.6	V
Base-Emitter Saturation Voltage (IC = 100 mA, I _B = 5.0 mA)(1)		V _{BE(sat)}	_	_	1.2	V
Base–Emitter On Voltage (I _C = 100 μA, V _{CE} = 5.0 V) (I _C = 2.0 mA, V _{CE} = 5.0 V) (I _C = 100 mA, V _{CE} = 5.0 V)(1)		VBE(on)	— 0.55 —	0.5 0.62 0.83	 0.7 	V
DYNAMIC CHARACTERISTICS		•			•	•
Current-Gain — Bandwidth Product (I _C = 0.5 mA, V _{CE} = 3.0 V, f = 100 MHz)	BC182 BC183 BC184	fΤ	_ _ _	100 120 140	_ _ _	MHz
$(I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 100 \text{ MHz})$	BC182 BC183 BC184		150 150 150	200 240 280	_ _ _	
Common Base Output Capacitance (V _{CB} = 10 V, I _C = 0, f = 1.0 MHz)		C _{ob}	_	_	5.0	pF
Common Base Input Capacitance $(V_{EB} = 0.5 \text{ V}, I_C = 0, f = 1.0 \text{ MHz})$		C _{ib}	_	8.0	_	pF
Small–Signal Current Gain (I _C = 2.0 mA, V _{CE} = 5.0 V, f = 1.0 kHz)	BC182 BC183 BC184 BC182A BC182B	h _{fe}	125 125 240 125 240	_ _ _ _	500 900 900 260 500	_
Noise Figure $ \begin{array}{l} \text{(IC = 0.2 mA, V}_{\text{CE}} = 5.0 \text{ V, R}_{\text{S}} = 2.0 \text{ k}\Omega, \\ \text{f = 1.0 kHz)} \\ \text{(IC = 0.2 mA, V}_{\text{CE}} = 5.0 \text{ V, R}_{\text{S}} = 2.0 \text{ k}\Omega, \\ \text{f = 1.0 kHz, f = 200 Hz)} \\ \end{array} $	BC184 BC182 BC183 BC184	NF	1111	2.0 2.0 2.0 2.0	4.0 10 10 4.0	dB

^{1.} Pulse Test: Tp 300 s, Duty Cycle 2.0%.

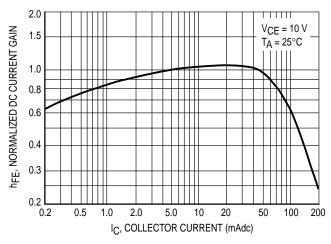


Figure 1. Normalized DC Current Gain

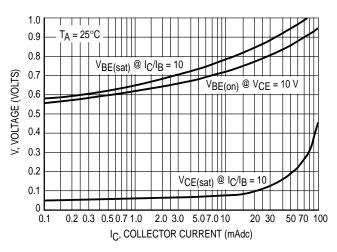


Figure 2. "Saturation" and "On" Voltages

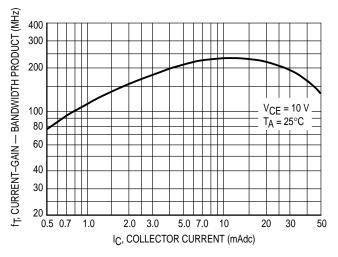


Figure 3. Current-Gain — Bandwidth Product

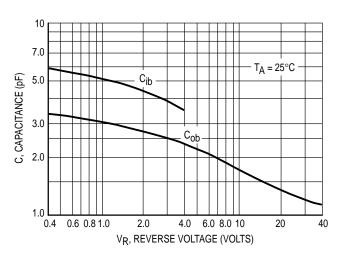


Figure 4. Capacitances

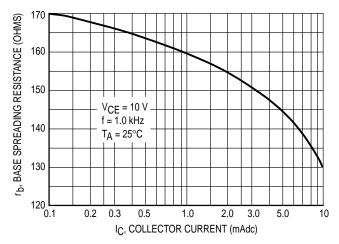
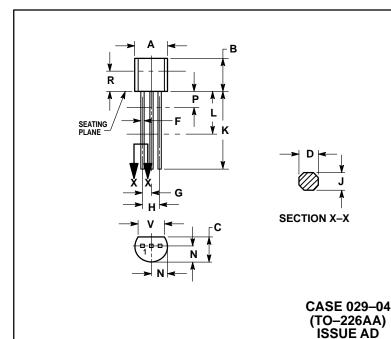


Figure 5. Base Spreading Resistance

PACKAGE DIMENSIONS



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L. DIMENSION F APPLIES BETWEEN F AIND L.
 DIMENSION D AND J APPLY BETWEEN L AND K
 MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
v	0.135		3 43	

STYLE 17:

PIN 1. COLLECTOR

2. BASE

3. EMITTER

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Datasheets for electronics components.

Amplifier Transistors

NPN Silicon

Features

• Pb-Free Package is Available*

MAXIMUM RATINGS

Rating	Symbol	BC182	Unit
Collector - Emitter Voltage	V_{CEO}	50	Vdc
Collector - Base Voltage	V_{CBO}	60	Vdc
Emitter – Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	Ic	100	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	350 2.8	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.0 8.0	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

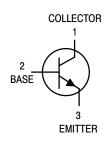
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

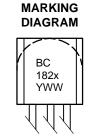
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	357	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	125	°C/W



http://onsemi.com







BC Specific Device Code

x A or B Y = Year WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping [†]
BC182	TO-92	5000 Units / Box
BC182G	TO-92 (Pb-Free)	5000 Units / Box
BC182A	TO-92	5000 Units / Box
BC182B	TO-92	5000 Units / Box
BC182BRL1	TO-92	2000 /Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS				•		
Collector – Emitter Breakdown Voltage $(I_C = 2.0 \text{ mA}, I_B = 0)$		V _{(BR)CEO}	50	_	_	V
Collector – Base Breakdown Voltage ($I_C = 10 \mu A, I_E = 0$)		V _{(BR)CBO}	60	_	_	V
Emitter – Base Breakdown Voltage ($I_E = 100 \mu A, I_C = 0$)		V _{(BR)EBO}	6.0	_	-	V
Collector Cutoff Current (V _{CB} = 50 V, V _{BE} = 0)		І _{СВО}	-	0.2	15	nA
Emitter–Base Leakage Current (V _{EB} = 4.0 V, I _C = 0)		I _{EBO}	-	_	15	nA
ON CHARACTERISTICS			-	=	-	-
DC Current Gain ($I_C = 10 \mu A, V_{CE} = 5.0 V$)	BC182	h _{FE}	40	_	_	_
$(I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$ $(I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC182 BC182A BC182B BC182		120 120 180 80	-	500 220 500	
Collector – Emitter On Voltage $(I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA})$ $(I_C = 100 \text{ mA}, I_B = 5.0 \text{ mA}) \text{ (Note 1)}$		V _{CE(sat)}		0.07 0.2	0.25 0.6	V
Base – Emitter Saturation Voltage (I _C = 100 mA, I _B = 5.0 mA) (Note 1)		V _{BE(sat)}	-	_	1.2	V
Base–Emitter On Voltage ($I_C = 100 \mu A, V_{CE} = 5.0 V$) ($I_C = 2.0 mA, V_{CE} = 5.0 V$) ($I_C = 100 mA, V_{CE} = 5.0 V$) (Note 1)		V _{BE(on)}	- 0.55 -	0.5 0.62 0.83	- 0.7 -	V
DYNAMIC CHARACTERISTICS				•	•	
Current – Gain — Bandwidth Product (I _C = 0.5 mA, V _{CE} = 3.0 V, f = 100 MHz)		f _T	_	100	_	MHz
$(I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 100 \text{ MHz})$			150	200	-	
Common Base Output Capacitance (V _{CB} = 10 V, I _C = 0, f = 1.0 MHz)		C _{ob}	-	-	5.0	pF
Common Base Input Capacitance (V _{EB} = 0.5 V, I _C = 0, f = 1.0 MHz)		C _{ib}	-	8.0	_	pF
Small–Signal Current Gain ($I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$)	BC182 BC182A BC182B	h _{fe}	125 125 240	- - -	500 260 500	-
Noise Figure (I _C = 0.2 mA, V_{CE} = 5.0 V, R_{S} = 2.0 k Ω , f = 1.0 kHz)		NF	-	2.0	10	dB

^{1.} Pulse Test: Tp 300 s, Duty Cycle 2.0%.

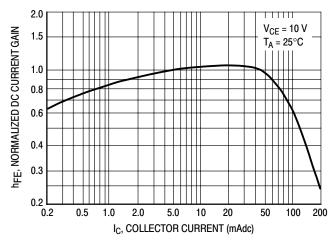


Figure 1. Normalized DC Current Gain

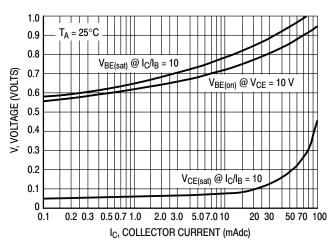


Figure 1. "Saturation" and "On" Voltages

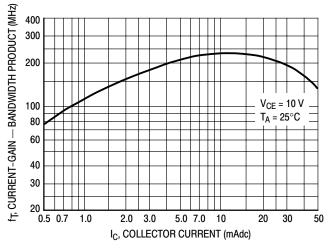


Figure 2. Current-Gain — Bandwidth Product

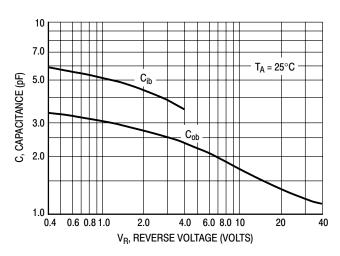


Figure 3. Capacitances

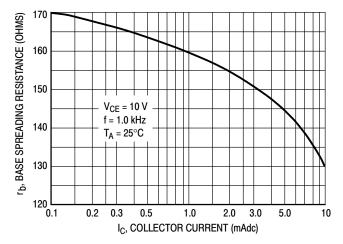
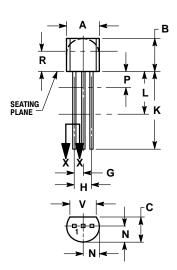


Figure 4. Base Spreading Resistance

PACKAGE DIMENSIONS

TO-92 TO-226AA CASE 29-11 **ISSUE AL**





- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND
- BEYOND DIMENSION K MINIMUM.

	INC	INCHES		IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

BASE EMITTER

STYLE 17: PIN 1. COLLECTOR

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